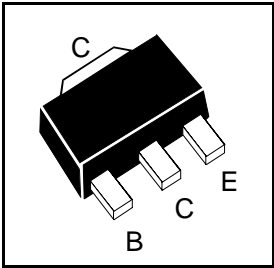


SOT89 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - OCTOBER 1995 

UCD: (Type) (Spec) (M)

BFN17



COMPLEMENTARY TYPE - BFN16
PARTMARKING DETAILS - DG

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-250	V
Collector-Emitter Voltage	V_{CEO}	-250	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-500	mA
Continuous Collector Current	I_C	-200	mA
Base Current	I_B	-100	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	-1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-250		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-250		V	$I_C = -1\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		-100 -20	nA μA	$V_{CB} = -250\text{V}$ $V_{CB} = -250\text{V}, T_{amb} = 150^\circ\text{C}$
Emitter Cut-Off Current	I_{EBO}		-100	nA	$V_{EB} = -3\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.4	V	$I_C = -20\text{mA}, I_B = -2\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -20\text{mA}, I_B = -2\text{mA}$
Static Forward Current Transfer Ratio	h_{FE}	25 40 40			$I_C = -1\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -10\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -30\text{mA}, V_{CE} = -10\text{V}^*$
Transition Frequency	f_T	Typ. 100		MHz	$I_C = -20\text{mA}, V_{CE} = -10\text{V}^*$ $f = 20\text{MHz}$
Output Capacitance	C_{obo}	Typ. 2.5		pF	$V_{CB} = -30\text{V}, f = 1\text{MHz}$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FMMTA92 datasheet